

FORM HDP-1449 (Based on Form PTO-1449)

**PATENT AND TRADEMARK OFFICE  
INFORMATION DISCLOSURE CITATION**  
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Sheet 1 of 2

ATTORNEY DOCKET NO.

5077-000073/COA

SERIAL NO.

APPLICANT

Toshiya Yokogawa, et al.

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2814

**U.S. PATENT DOCUMENTS**

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.		3,739,243	6/12/1973	Semichon, et al.		
2.		4,882,609	11/21/1989	Schubert, et al.		
3.		6,388,272	5/14/2002	Odekirk		
4.		5,488,237	1/30/1996	Kuwata [New art]		

**FOREIGN PATENT DOCUMENTS**

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.		WO 01/67521 A1	9/13/2001	WIPO		Abstract	
2.		WO 01/93339 A1	12/6/2001	WIPO		Abstract	
3.		EP 0612104 A2	8/24/1994	Europe		Abstract	
4.		JP 54-132173	10/13/1979	Japan		Abstract	
5.		JP 5-13446	1/22/1993	Japan		Abstract	
6.		JP 6-349860	12/22/1994	Japan		Abstract	
7.		JP 9-289216	11/4/1997	Japan		Abstract	
8.		EP 0555886 A2	8/18/1993	Europe [New art]			

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)**

Ref. Desig.	Examiner's Initials	
1.		D.W. Van der Weide, "Delta-doped Schottky diode nonlinear transmission lines for 480-fs, 3.5-V transients", Applied Physics Letters, Vol. 65, No. 7, 15 August 1994, pp. 881-883.

Date Considered:

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EXAMINER: Please initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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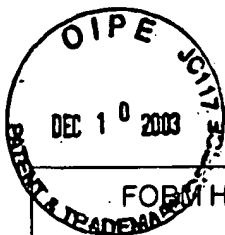
**OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)**

Ref. Desig.	Examiner's Initials	
2.		A. Konstantinov, et al., "Investigation of lo-hi-lo and delta-doped silicon carbide structures", Mat. Res. Soc. Symp. Proc. Vol. 640, 2001, pp. H2.4.1-6.
3.		Shui Jinn Wang, et al., "Schottky/Two-Dimensional Hole Gas Silicon Barrier Diodes with Single and Coupled Delta-Doped Wells", Jpn. J. Appl. Phys. Vol. 33, No. 4B, Part 1, 1 April 1994, pp. 2429-2434.
4.		W.C. Hsu, et al., "A Quantum Well- doped GaAs Fet Fabricated by Low-Pressue Metal Organic Chemical Vapro Deposition", Solid-State Electronics, Vol. 34, No. 6, 1 June 1991, pp. 649-653.
5.		S.M. Bedair, "Selective-area and sidewall growth by atomic layer epitaxy", Semiconductor Science and Technology, Vol. 8, No. 6, 1 June 1993, pp. 1052-1062.
6.		European Patent Publication No. EP 0 309 290 A1
7.		"Characterization of Double Pulse-Doped Channel GaAs MESFET's", Shigeru Nakajima, et al., IEEE Electron Device Letters, Vol. 14, No. 3, March 1993, pp. 146-148.
8.		"Stark Effect Studied in -doped GaAs Structures", A. Ben Jazia, et al., Semicond. Sci. Technol. 12 (1997), pp. 1388-1395.
9.		"Vertical Hot-Wall Type CVD for SiC Growth", Kunimasa Takahashi, et al., Materials Science Forum Vols. 338-342 (2000), pp. 141-144.
10.		"Electronic Properties of Nitrogen Delta-Doped Silicon Carbide Layers", Toshiya Yokogawa, et al., Mat. Res. Soc. Symp. Proc. Vol. 640 (2001), pp. H2.5.1-H2-5-6.
11.		Partial Supplementary European Search Report EP 00 97 6350, 12/20/2002.

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Toshiya Yokogawa et al.

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July 23, 2003

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**U.S. PATENT DOCUMENTS**

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.		5,493,136	02/20/1996	Matsuzaki et al.		

**FOREIGN PATENT DOCUMENTS**

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.		06310536 A	11/04/1994	Japan		*	

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)**

Ref. Desig.	Examiner's Initials	
1.		Preliminary Manuscript of the 45 <sup>th</sup> Lecture Presentation by Japan Society of the Applied Physics, Volume No. 1, page 422, 30p-YG-4, March 28, 1998.
2.		Notice of Reasons of Rejection for Japanese Patent App. No. 2001-566193 mailed September 16, 2003, and English translation.

\*Japanese Patent App. No. 06310536 A corresponds to U.S. Patent No. 5,493,136.

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